

Schottky Barrier Diode

Features

1. High reliability
2. Low reverse current and low forward voltage

Applications

Low current rectification and high speed switching

Construction

Silicon epitaxial planar

Absolute Maximum Ratings

$T_a=25^{\circ}\text{C}$

Parameter	Symbol	Limits	Unit
Peak reverse voltage	V_{RM}	40	V
DC reverse voltage	V_R	40	V
Mean rectifying current	I_O	0.1	A
Peak forward surge current	I_{FSM}	1	A
Junction temperature	T_j	125	$^{\circ}\text{C}$
Storage temperature	T_{stg}	-40~+125	$^{\circ}\text{C}$

Electrical Characteristics

$T_a=25^{\circ}\text{C}$

Parameter	Symbol	Conditions	Min	Type	Max	Unit
Forward voltage	V_{F1}	$I_F=10\text{mA}$	-	0.28	0.34	V
Forward voltage	V_{F2}	$I_F=100\text{mA}$	-	0.45	0.55	V
Reverse current	I_R	$V_R=40\text{V}$	-	9.0	100	μA
Capacitance between terminals	C_T	$V_R=10\text{V}, f=1\text{MHz}$	-	6.0	-	pF

Characteristics (Ta=25°C unless specified otherwise)

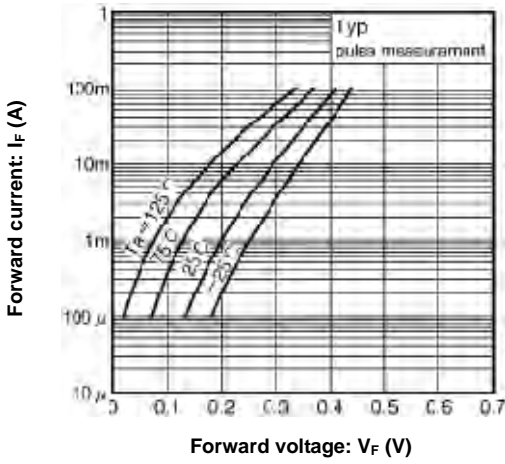


Figure 1. Forward characteristics

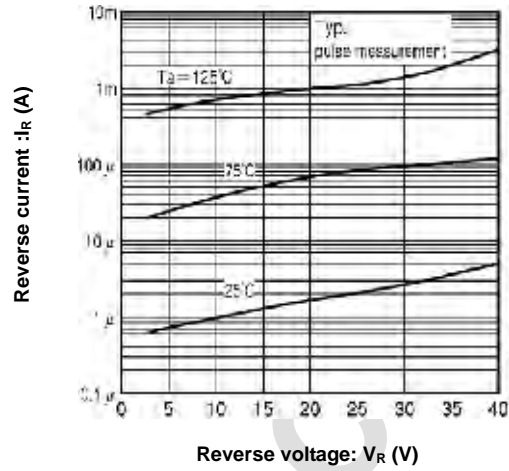


Figure 2. Reverse characteristics

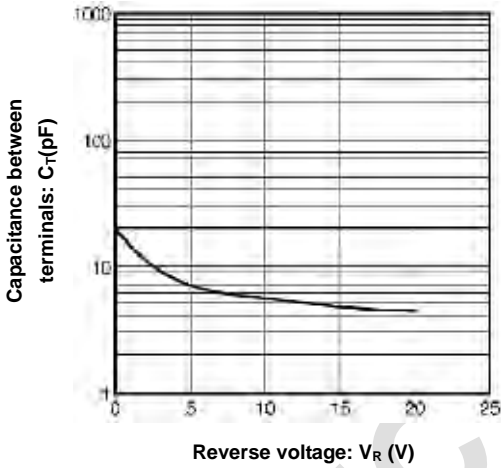


Figure 3. Capacitance between terminals characteristics

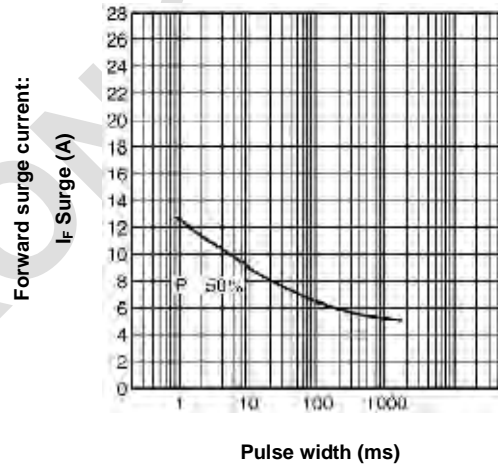


Figure 4. Forward surge current characteristics

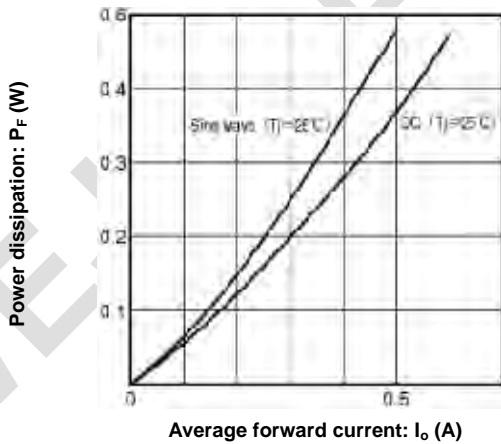


Figure 5. Mean rectifying current characteristics

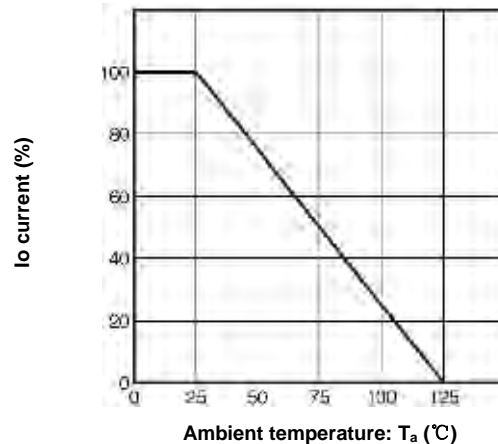
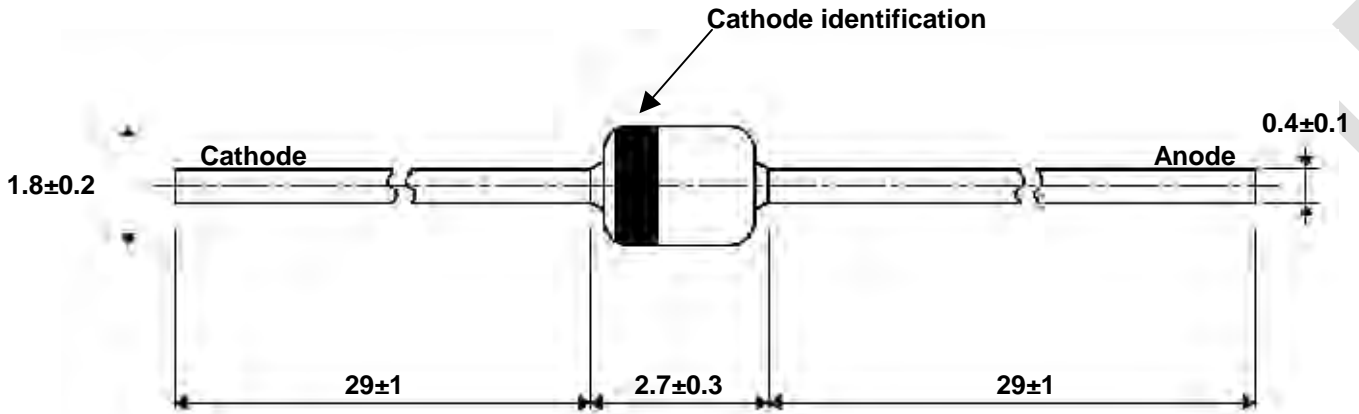


Figure 6. Derating curve (mounting on glass epoxy PCBs)

Dimensions in mm



Standard Glass Case
JEDEC DO 34